

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

BU526 BU526A

DESCRIPTION

- With TO-3 package
- Short switching times.
- High dielectric strength.

APPLICATIONS

- For use in power supply units of TV receives.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

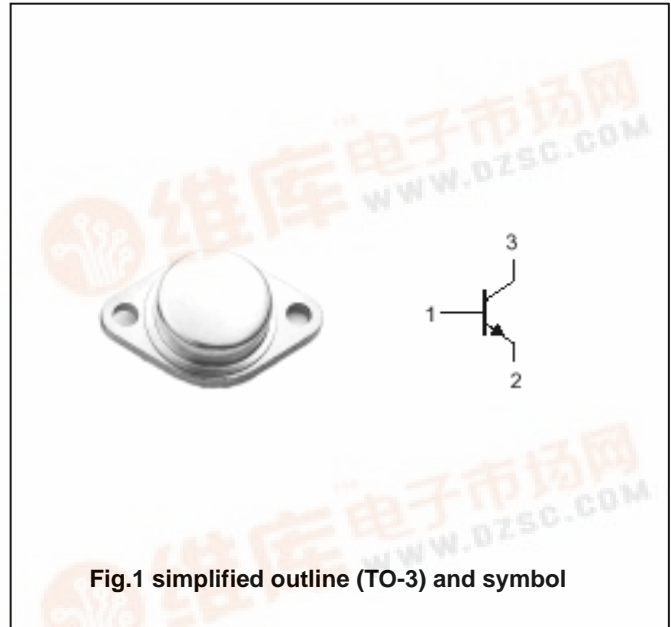


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	Open emitter	900	V
V _{CEO}	Collector-emitter voltage	BU526	400	V
		BU526A	460	
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		8	A
I _{CM}	Collector current-peak		10	A
P _T	Total power dissipation	T _C =25	86	W
T _j	Junction temperature		175	
T _{stg}	Storage temperature		-65~175	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	1.04	/W

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BU526 BU526A

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	BU526	I _C =50mA; I _B =0;	400			V
		BU526A		460			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =10mA; I _C =0;	7			V
V _{CEsat-1}	Collector-emitter saturation voltage		I _C =5A; I _B =1 A			1.5	V
V _{CEsat-2}	Collector-emitter saturation voltage		I _C =8A; I _B =3 A			5.0	V
V _{BEsat}	Base-emitter saturation voltage		I _C =5A; I _B =1 A			1.6	V
I _{CBO}	Collector cut-off current		V _{CB} =900V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current		V _{EB} =7V; I _C =0			0.1	mA
h _{FE}	DC current gain		I _C =1A; V _{CE} =5V	15		45	

PACKAGE OUTLINE

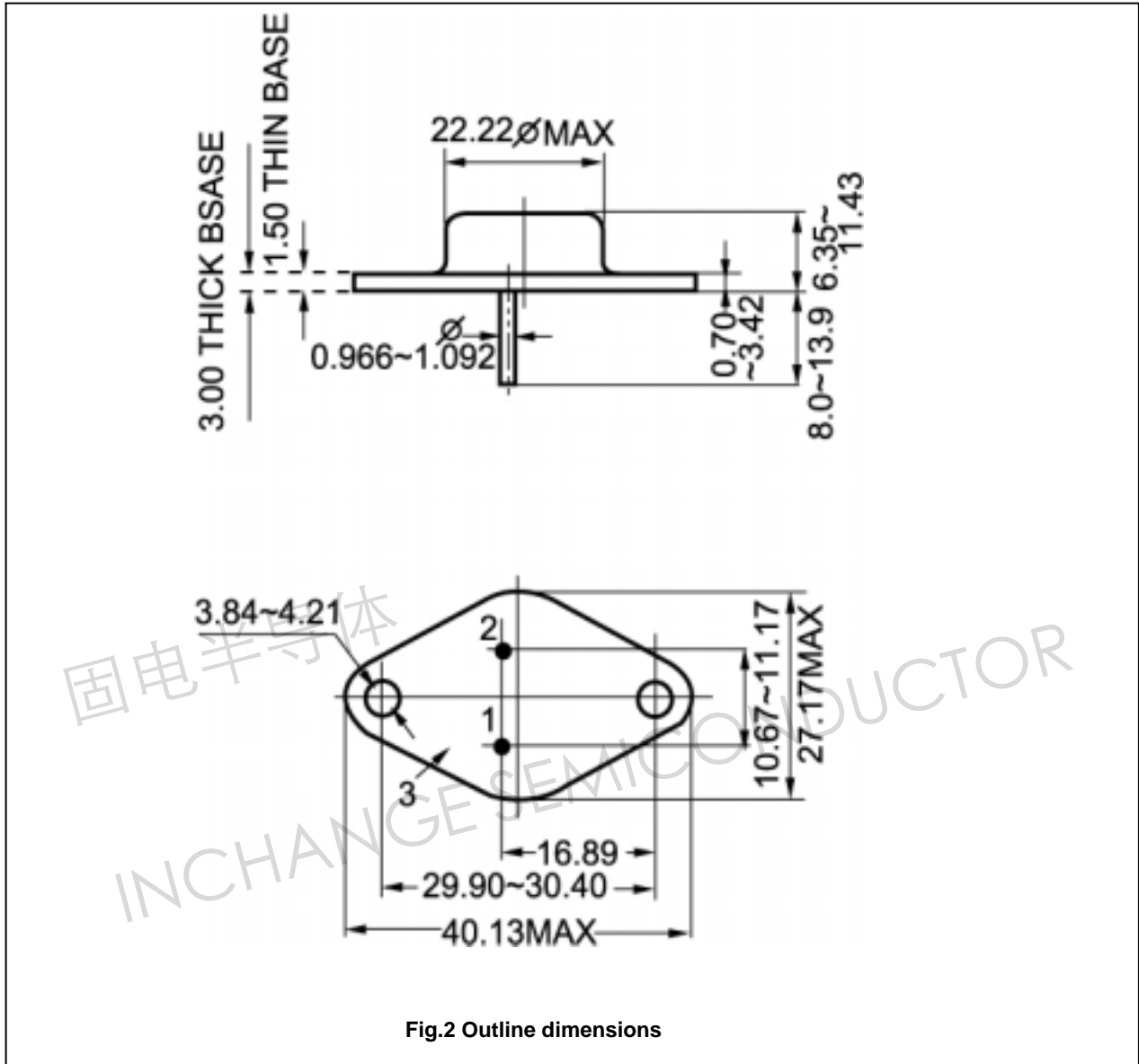


Fig.2 Outline dimensions